

**STRAINED LAYER InGaAs/GaAs SINGLE QUANTUM  
WELL LASERS UNDER HIGH INJECTION.**

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The dissertation "Strained layer InGaAs/GaAs single quantum well lasers under high injection" by Raghuraman Ranganathan has been examined and approved by the following Examination Committee:

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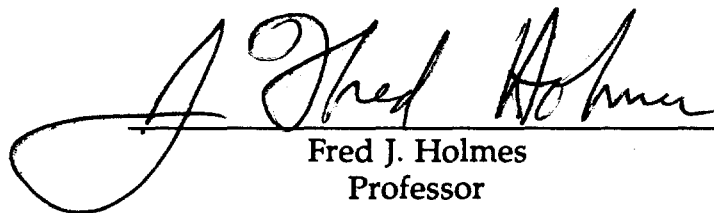
Kirk P. Boyer  
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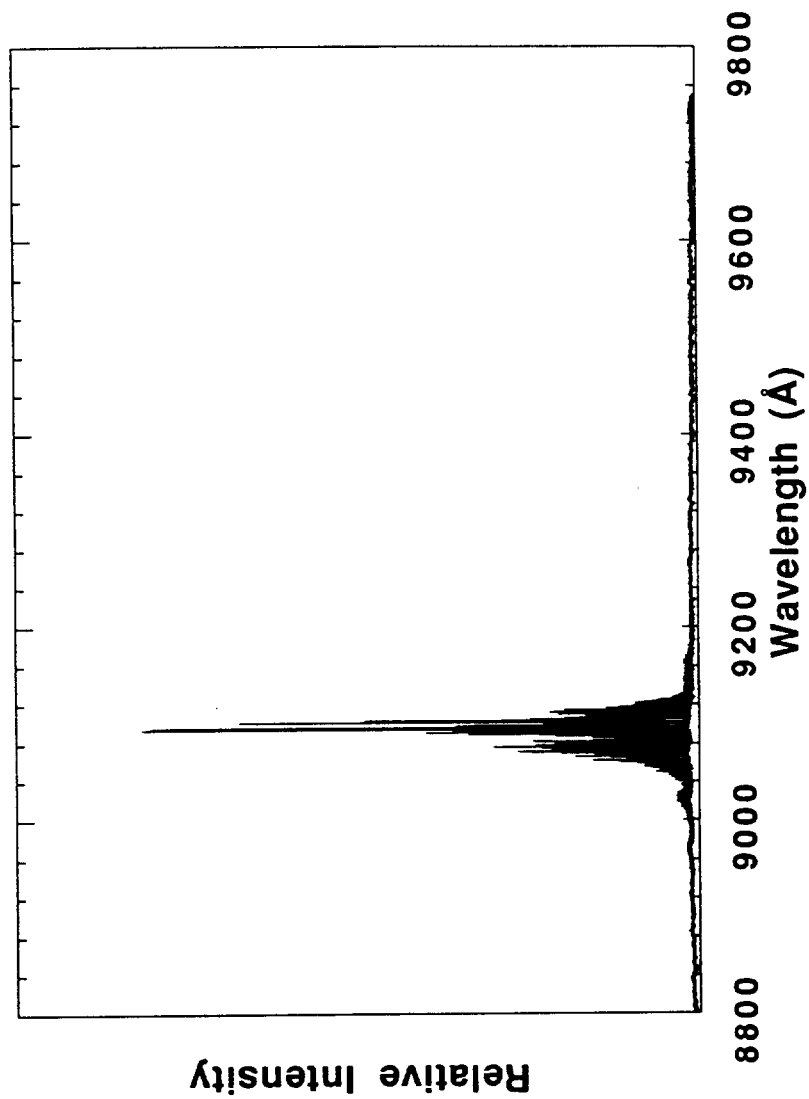


Figure 3.23. Intensity spectrum at  $I = 400$  mA for the  $15 \mu\text{m} \times 575 \mu\text{m}$  device.



































































































































































































